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REMARKS

Claims 1-24 currently are pending, of which claims 4-9 are presently withdrawn from consideration. By the present response, claims 1-3, 11-16 and 18-24 are amended. In view of the above amendments and the remarks advanced below, Applicants respectfully request reconsideration and withdrawal of the rejections of the claims.

In the final Office Action, the Examiner maintains the rejection of claims 1, 11-16, 18 and 21-24, under 35 U.S.C. § 102(b) as allegedly being anticipated by Kim (U.S. Patent No. 5,877,512), the rejection of claims 2, 3, 19 and 20 under 35 U.S.C. §103 as allegedly being obvious over the Kim patent in view of Japanese patent publication no. [4]04152676A (hereinafter, “the ‘676 document”), and the rejection of claims 10 and 17 under 35 U.S.C. §103 as allegedly being obvious over Kim in view of Japanese patent publication no. 2001028338 (hereinafter, “the ‘338 document”). With respect to Applicants’ detailed arguments explaining where a channel region appears formed in the transistor shown in Figure 3 of the Kim patent, the Examiner responds as follows:

However, see Kim, column 3, lines 62-67, wherein layer 27 is referred to as: “...where a channel of the transistor is formed...”, i.e., a channel forming region. (See, page 4, lines 3-6.)

However, a key word in the above-quoted text of Kim is “where.” That is, the place or region in which the channel is formed. The Kim document does not explicitly describe this location, and as Applicants pointed out in the January 19, 2006, response.

It is respectfully submitted that those of ordinary skill in the art would understand that the term “channel forming region” corresponds to a region formed between the source and drain regions of the transistor when a channel is formed by way of an applied gate potential. Applicants appreciate that Figure 3 of Kim discloses the channel layer 27, the gate electrode 21, the source electrode 25, and the drain electrode 23. However, Kim does not clearly show where a channel forming region corresponding to the claimed channel region is located in the layer 27. Additionally, those of ordinary skill in the art would understand that carrier flow in the channel is along the length direction of any channel formed within the channel layer 27 of Kim, and that the region in which the channel is formed in the device of Kim’s Figure 3 would be that shown in the annotated attachment to the January 16, 2006 response.

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It appears from the above-quoted statement of the Examiner that he considers the entire layer 27 a "channel forming region." However, Applicants submit that such an interpretation would not be reasonable because those of ordinary skill in the art would understand that a channel is not formed in the entire channel layer 27 of Kim, and thus that the meaning of "channel forming region" in the field of the invention would not correspond to those parts or regions of the layer 27 of Kim in which a channel is not formed. It is respectfully submitted, therefore, that the Examiner twists the meaning of the claim term "channel forming region" beyond that which one of ordinary skill would consider reasonable, and in such a way that only serves the Examiner's zeal to maintain the present rejections.

However, in an effort to advance the prosecution of this application, Applicants have amended the claims to make abundantly clear the distinctions pointed out in Applicants January 19, 2006, response, the remarks of which are hereby incorporated by reference. More particularly, claims 1-3 are amended to recite an active layer formed in the TFT, source and drain regions formed in the active layer, and a channel forming region formed in the active layer and between the source and drain regions. Also, claims 11-16 are amended to recite that a channel forming region is formed between the source and drain regions. Support for these amendments are found throughout Applicants' original disclosure, for example, in Figures 1A-1C, 5A-6D, 15A-17E and the corresponding description in the specification. It is respectfully submitted that the Kim patent, the '676 document, and the '338 document, whether considered individually or in combination, fail to teach or suggest these features, as set forth in the independent claims.

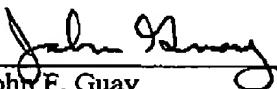
Also, Kim fails to disclose that the channel region, and the source and drain regions are formed within one layer, namely, the active layer, as recited in claims 1-3, or the semiconductor layer, as recited in claims 11-16. Furthermore, none of the applied documents teach or suggest the claimed relationship between the channel width direction and a concave or convex portion as recited in claims 1-3, and a concave or convex portion and the carrier flow direction as recited in claims 11-16. For these additional reasons, claims 1-3 and 11-16 are allowable.

Dependent claims 10 and 17-24 depend from one of independent claims 1-3 and 11-14, and are therefore allowable at least for the above reasons, and further for the additional features recited.

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Based on the foregoing, it is respectfully submitted that all the pending rejections under 35 U.S.C. 102 and 103 should be withdrawn and the application passed to issue. Prompt notification of the same is earnestly sought.

Respectfully submitted,


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